

# applied surface science

A journal devoted to the properties of interfaces  
in relation to the synthesis and behaviour of materials

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A JOURNAL DEVOTED TO THE PROPERTIES OF INTERFACES  
IN RELATION TO THE SYNTHESIS AND BEHAVIOUR OF MATERIALS

Editors:

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## INSTRUCTIONS FOR AUTHORS

Contributions must be written in English and should have an abstract. The original manuscript (with original figures) and two duplicate copies should be submitted to one of the Editors. Micrographs should be submitted in triplicate. See inside front cover for the addresses.

**Rapid publication:** Short papers, for which rapid publication is appropriate, may be submitted as a "Letter". The manuscripts should not exceed 1000 words in length, contain a modest number of illustrations and a short abstract.

**Length of manuscript:** Typically 10 pages of manuscript and 4 figures will produce roughly 5 printed pages (count title page, text pages, tables and figure captions as manuscript pages).

**Page charge and reprints:** There is no page charge and 25 reprints of the article will be supplied free of charge. Additional reprints may be ordered from the publisher. An order form will be sent to contributors together with the proofs.

### Preparation of manuscripts

Manuscripts should be typed throughout with double line spacing and wide margins on numbered pages.

The *title page(s)* should contain, in addition to the article title, author(s)' names and affiliations, the text of related footnotes and the text of the abstract. Indicate which author will act as contact author and *provide FAX No., telephone No. and telex No.*, if available.

*Tables* should be typed on separate sheets at the end of the manuscript. In addition to its serial number, each table should have a sufficiently detailed heading or caption to explain the data displayed in it.

*Figures* should be numbered and their captions listed together at the end of the manuscript.

*References* in the text to other publications should be numbered consecutively within square brackets, for example: "Chang and Weaver [1] have shown ..." and listed together at the end of the text, for example:

- [1] S.-C. Chang and M.J. Weaver, *Surf. Sci.* 241 (1991) 11.
- [2] S.J. Hoekje and G.B. Hoflund, *Appl. Surf. Sci.* 47 (1991) 43.
- [3] F.J. Himpsel, *Surf. Sci. Rep.* 12 (1990) 1.
- [4] A. Roth, *Vacuum Technology*, 3rd ed. (North-Holland, Amsterdam, 1990).
- [5] V. Celli, in: *Dynamical Properties of Solids*, Vol. 6, Eds. G.K. Horton and A.A. Maradudin (North-Holland, Amsterdam, 1990) p. 337.

References to unpublished or not readily accessible reports should be avoided. In the case of multiple authorship all authors should be listed in the references provided they number less than ten. Only in the case of more than ten authors is the first author et al. acceptable.

*Formulae* in the manuscript should be typed with particular consideration given to characters that may be misinterpreted, e.g.

I (cap.), l (el), 1 (one), ' (prime)	c, C; k, K, $\kappa$ (kappa); p, P, $\rho$ (rho)
o (lower case), O (cap.), 0 (zero), ° (deg)	u, v (lower case), $\nu$ (nu), V (cap.)
× (times), x (lower case), X (cap.)	$\Sigma$ (sigma), $\Sigma$ (sum); $\Pi$ (pi), $\Pi$ (product); etc.

If necessary, unusual symbols should be explained in pencil in the margin.

*Vectors* should be indicated by a wavy underlining, and will be printed in bold-face italics.

### Preparation of figures

The publisher requires a set of good quality drawings and photographs to produce the printed line figures and half-tone plates in the journal. Photographic copies ("glossy prints") of drawings are also acceptable for the line figures if they have been sharply focused and evenly exposed. **As a rule, Xerox copies cannot be accepted.** Original drawings and photographs will be returned after publication of the paper.

**Line figures:** The drawings or glossy prints supplied for the line figures should be 1.5–3 times larger than the printed size of the figures and should contain all the required, carefully applied lettering.

Figures are preferably reduced to a single column width (7.6 cm) unless their complexity, large width-to-height ratio, or need to display special detail makes a larger format necessary (max. printed width ~ 20 cm). Inappropriately sized lettering on a figure may prevent its reduction to the size optimum for its information content. The lettering used on a drawing should be chosen so that after reduction, the height of numbers and (capital) letters falls within the range 1.2–2.4 mm. Care should be exercised in choosing the pen width of machine-plotted graphs. Frequently lines in these figures are too fine compared to the area of the figure.

Shaded areas in line figures should be shown by means of cross-hatching (or a matrix of dots) rather than a continuous grey "wash". Cross-hatching, after reduction, of density less than ~ 25 lines/cm is satisfactory.

**Half-tone plates:** The photographs supplied for reproduction should be unmounted unless they form part of a composite figure and they should have a somewhat greater contrast than is desired in the printed figure. It is important that the photographs supplied are not already screened (overprinted with the point-matrix used by printers) or moiré patterns will form when they are screened for a second time. When necessary, the top side of a photograph should be marked on the back. A reduction factor should be recommended for a photo when it is not obvious what detail in the photo is of interest.

**Colour plates:** Illustrations can be printed in colour when they are judged by the Editor to be essential to the presentation. The Publisher and the Author will each bear part of the extra costs involved. Further information concerning colour illustrations and the costs to the author can be obtained from the Publisher.

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